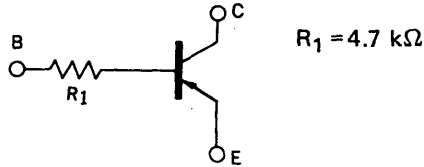


NEC

PNP SILICON TRANSISTOR AN1L3Z

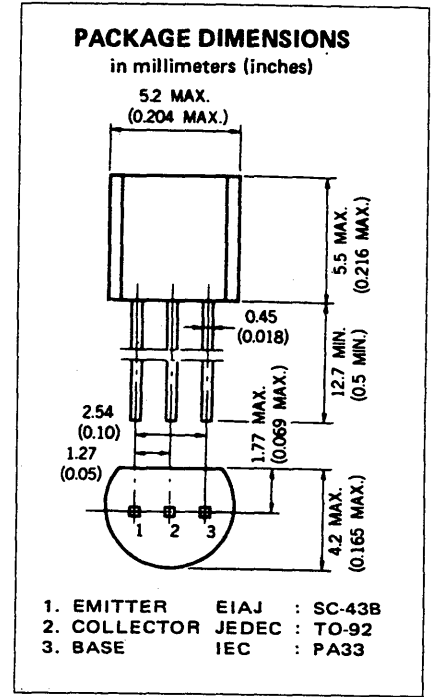
DESCRIPTION The AN1L3Z is designed for use in medium speed switching circuit.

FEATURE • Bias resistors built-in type PNP transistor equivalent circuit.



ABSOLUTE MAXIMUM RATINGS

- Maximum Temperatures**
- Storage Temperature -55 to +150 °C
 - Junction Temperature 150 °C Maximum
- Maximum Power Dissipation (T_a = 25 °C)**
- Total Power Dissipation 300 mW
- Maximum Voltages and Currents (T_a = 25 °C)**
- V_{CBO} Collector to Base Voltage -60 V
 - V_{CEO} Collector to Emitter Voltage -50 V
 - V_{EBO} Emitter to Base Voltage -5.0 V
 - I_{C(DC)} Collector Current (DC) -100 mA
 - I_{C(pulse)} Collector Current (pulse) -200 mA



ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
R ₁	Input Resistance	3.29	4.7	6.11	kΩ	
V _{IL}	Low Level Input Voltage		-0.57	-0.5	V	V _{CE} = -5.0 V, I _C = -100 μA
V _{IH}	Hi Level Input Voltage	-1.2	-0.75		V	V _{CE} = -0.2 V, I _C = -5.0 mA
t _{on}	Turn On Time		0.04	0.2	μs	V _{CC} = -5.0 V, R _L = 1.0 kΩ, V _{in} = -5.0 V, PW = 2 μs, Duty Cycle ≤ 2%
t _{stg}	Storage Time		1.7	5.0	μs	
t _{off}	Turn Off Time		1.9	6.0	μs	
h _{FE1}	DC Current Gain	135	260	600	-	V _{CE} = -5.0 V, I _C = -5.0 mA
h _{FE2}	DC Current Gain	100	200		-	V _{CE} = -5.0 V, I _C = -50 mA
V _{CE(sat)}	Collector Saturation Voltage		-0.04	-0.2	V	I _C = -5.0 mA, I _B = -0.25 mA
I _{CBO}	Collector Cutoff Current			-0.1	μA	V _{CB} = -50 V, I _E = 0

TYPICAL CHARACTERISTICS ($T_a = 25\text{ }^\circ\text{C}$)

